

Switchmode Full Plastic Dual Schottky Barrier Power Rectifiers

Using the Schottky Barrier principle with a refractory barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

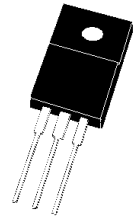
Features

- * Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- * Low Power Loss & High efficiency.
- * 150°C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory
Flammability Classification 94V-O
- * Pb free
- * In compliance with EU RoHs directives

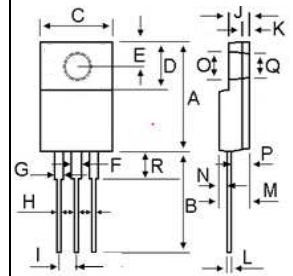


SCHOTTKY BARRIER RECTIFIERS

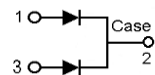
**20 AMPERES
45 VOLTS**



ITO-220AB



DIM	MILLIMETERS	
	MIN	MAX
A	14.80	16.10
B	12.65	14.40
C	9.70	10.36
D	4.60	6.80
E	2.50	3.50
F	0.90	1.45
G	0.90	1.45
H	0.50	0.90
I	2.40	2.70
J	2.34	3.30
K	0.55	1.30
L	0.36	0.80
M	4.20	4.90
N	1.10	1.80
O	2.90	3.50
P	2.30	3.15
Q	2.90	3.50
R	2.80	4.85



MAXIMUM RATINGS

Characteristic	Symbol	SRF2045C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
RMS Reverse Voltage	$V_{R(RMS)}$	32	V
Average Rectifier Forward Current (per diode) Total Device (Rated V_R)	$I_{F(AV)}$	10 20	A
Peak Repetitive Forward Current (Rate V_R , Square Wave, 20kHz)	I_{FM}	20	A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-wave, single phase, 60Hz)	I_{FSM}	200	A
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Maximum Instantaneous Forward Voltage ($I_F = 10$ Amp $T_C = 25^\circ\text{C}$) ($I_F = 10$ Amp $T_C = 125^\circ\text{C}$)	V_F	---	0.52 0.48	0.60 ---	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25^\circ\text{C}$) (Rated DC Voltage, $T_C = 125^\circ\text{C}$)	I_R	---	0.05 30	0.5 ---	mA

FIG-1 FORWARD CURRENT DERATING CURVE

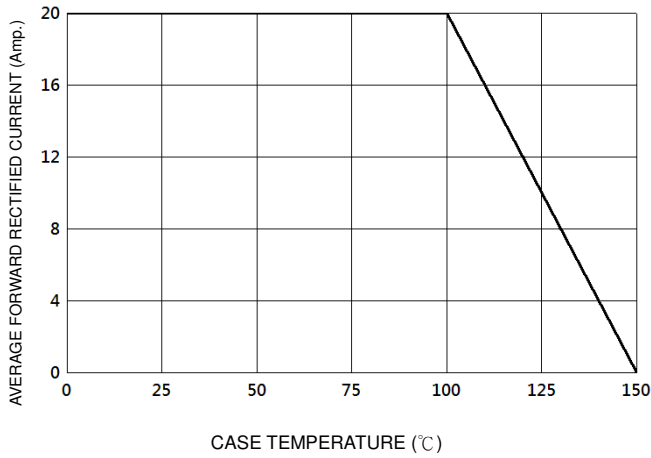


FIG-2 TYPICAL FORWARD CHARACTERISTICS

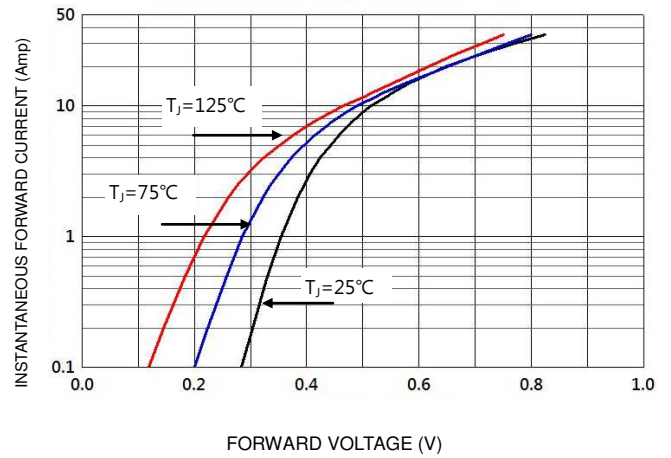


FIG-3 TYPICAL REVERSE CHARACTERISTICS

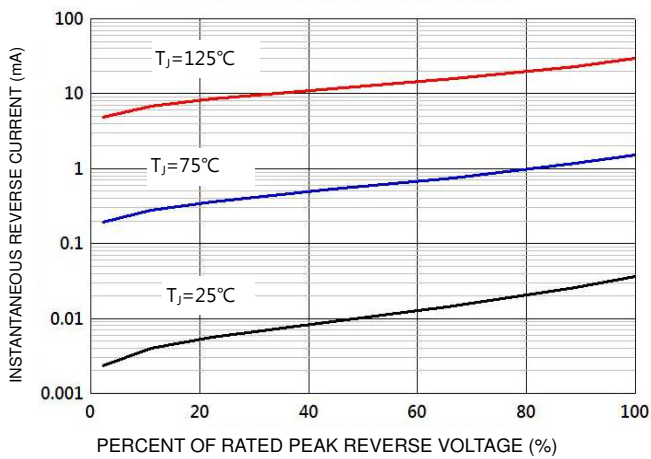


FIG-4 TYPICAL JUNCTION CAPACITANCE

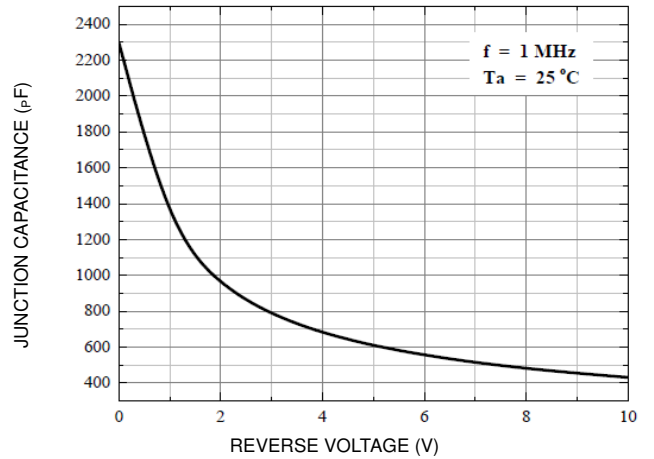
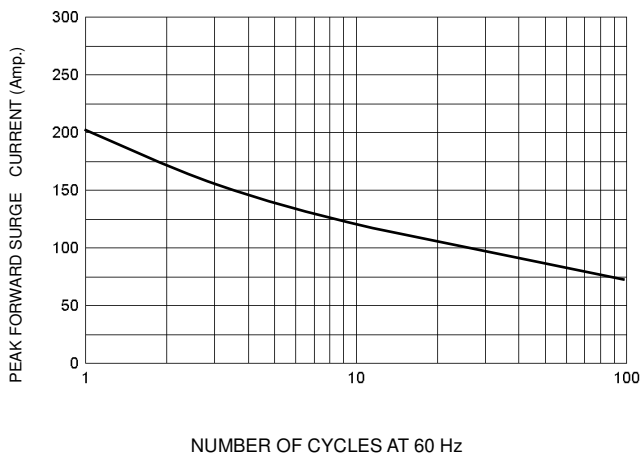


FIG-5 PEAK FORWARD SURGE CURRENT



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